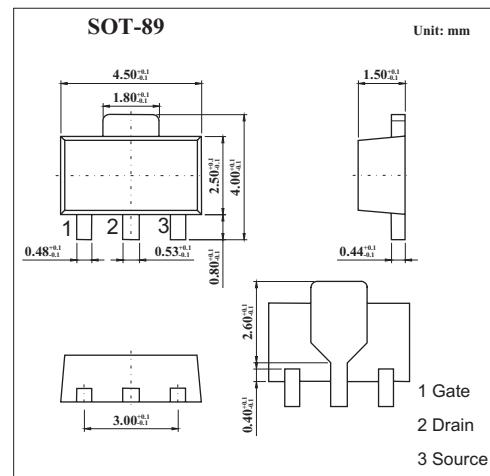


## MOS Field Effect Transistor

## 2SK1584

## ■ Features

- Directly driven by Ics having a 5V P
  - Has low on-state resistance
- $R_{DS(on)}=2.0\ \Omega$  MAX. @  $V_{GS}=4.0V, I_D=0.3A$
- $R_{DS(on)}=1.5\ \Omega$  MAX. @  $V_{GS}=10V, I_D=0.3A$

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Drain to source voltage	$V_{DSS}$	30	V
Gate to source voltage	$V_{GSS}$	$\pm 20$	V
Drain current (DC)	$I_D$	$\pm 0.5$	A
Drain current(pulse) *	$I_D$	$\pm 1.0$	A
Power dissipation	$P_D$	2.0	W
Channel temperature	$T_{ch}$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

\*  $PW \leqslant 10ms$ , duty cycle  $\leqslant 5\%$

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0$			10	$\mu A$
Gate leakage current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0$			$\pm 10$	$\mu A$
Gate to source cutoff voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=0.1mA$	1.3	1.85	2.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=5.0V, I_D=0.5A$	350	440		ms
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.0V, I_D=0.3A$		1.2	2.0	$\Omega$
		$V_{GS}=10V, I_D=0.3A$		0.65	1.5	$\Omega$
Input capacitance	$C_{iss}$	$V_{DS}=5.0V, V_{GS}=0, f=1MHz$		60		pF
Output capacitance	$C_{oss}$			50		pF
Reverse transfer capacitance	$C_{rss}$			9		pF
Turn-on delay time	$t_{d(on)}$	$I_D=0.3A, V_{GS(on)}=4V, R_L=33\Omega, V_{DD}=10V, R_G=10\Omega$		80		ns
Rise time	$t_r$			270		ns
Turn-off delay time	$t_{d(off)}$			100		ns
Fall time	$t_f$			110		ns

## ■ Marking

Marking	NH
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